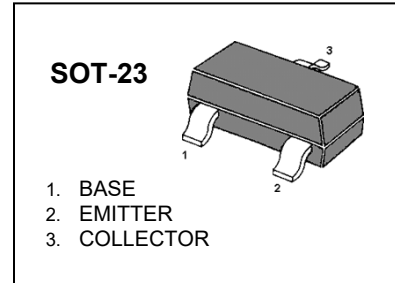


MMBT4403 TRANSISTOR (PNP)

FEATURES

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (MMBT4403)
- Ideal for Medium Power Amplification and Switching

MARKING : 2T



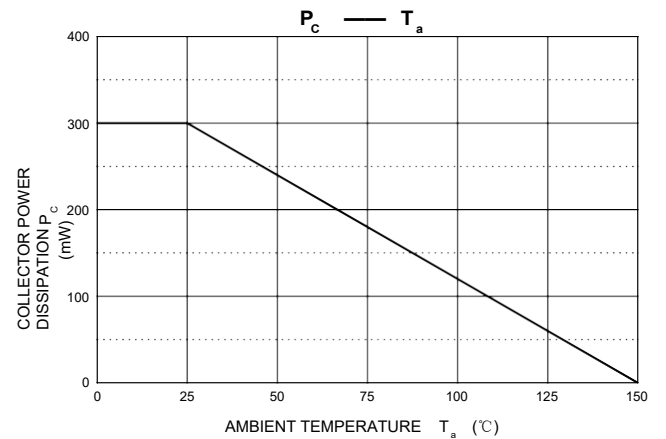
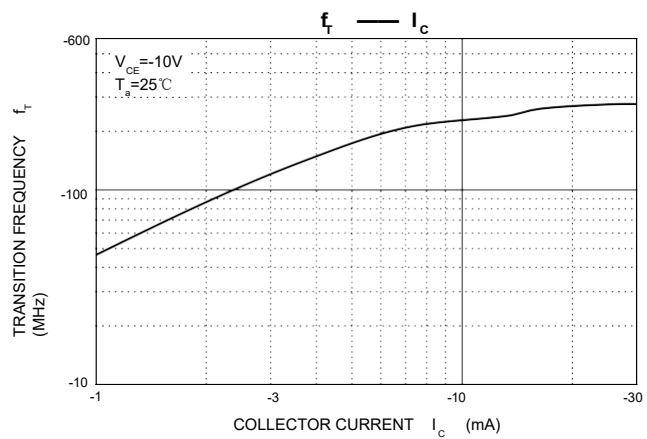
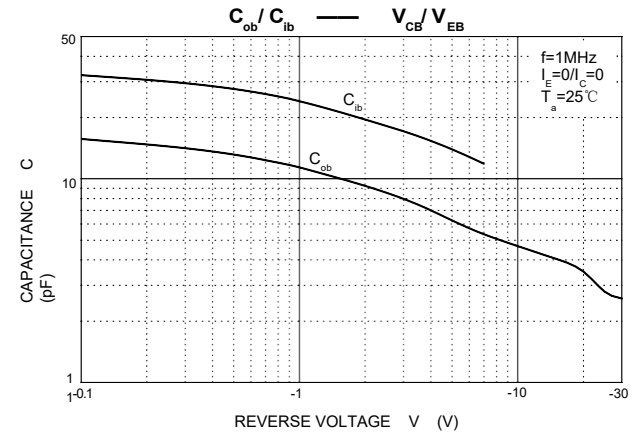
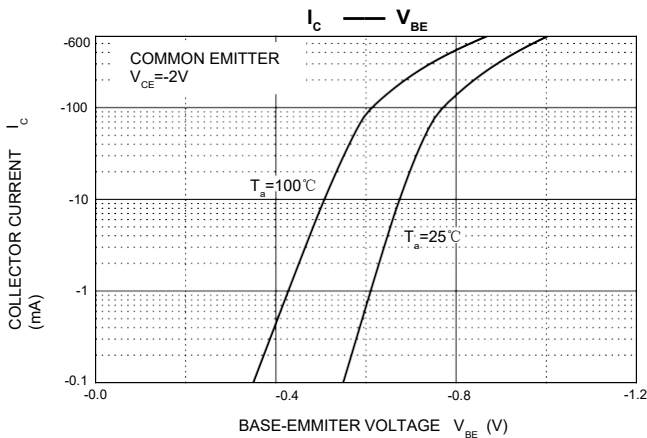
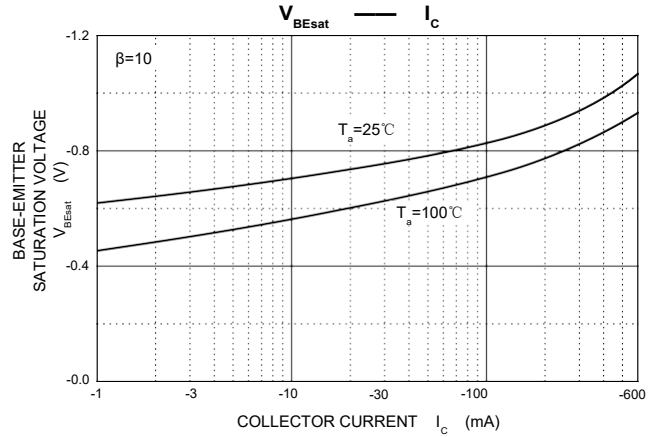
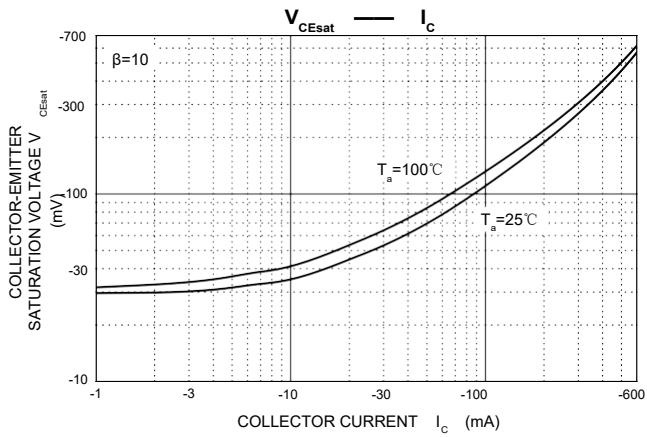
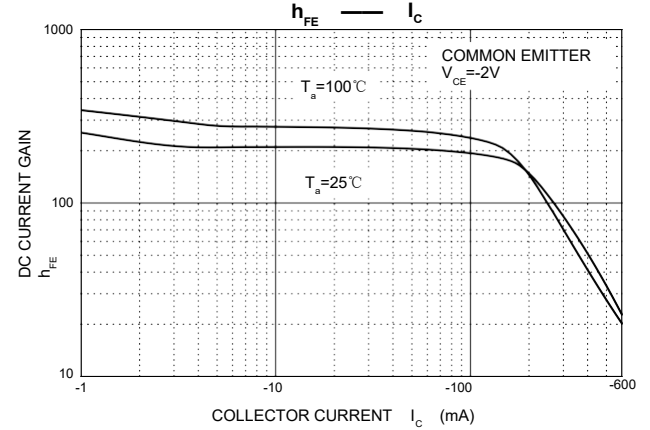
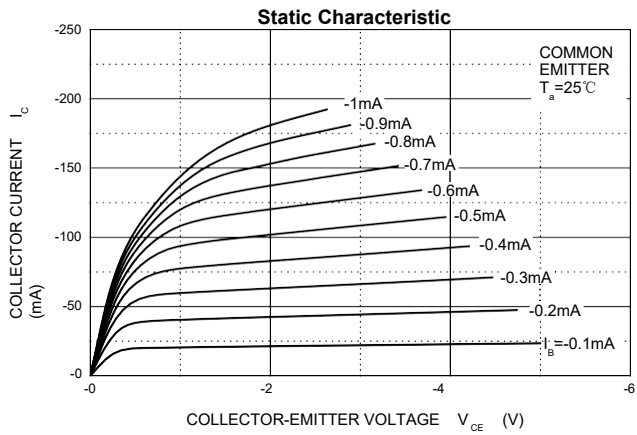
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.6	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu\text{A}, I_E=0$	-40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_C=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-35\text{V}, I_E=0$		-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=-35\text{V}, I_B=0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-4\text{V}, I_C=0$		-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-2\text{V}, I_C=-150\text{mA}$	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-150\text{mA}, I_B=-15\text{mA}$		-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-150\text{mA}, I_B=-15\text{mA}$		-0.95	V
Transition frequency	f_T	$V_{CE}=-10\text{V}, I_C=-20\text{mA}$ $f=100\text{MHz}$	200		MHz

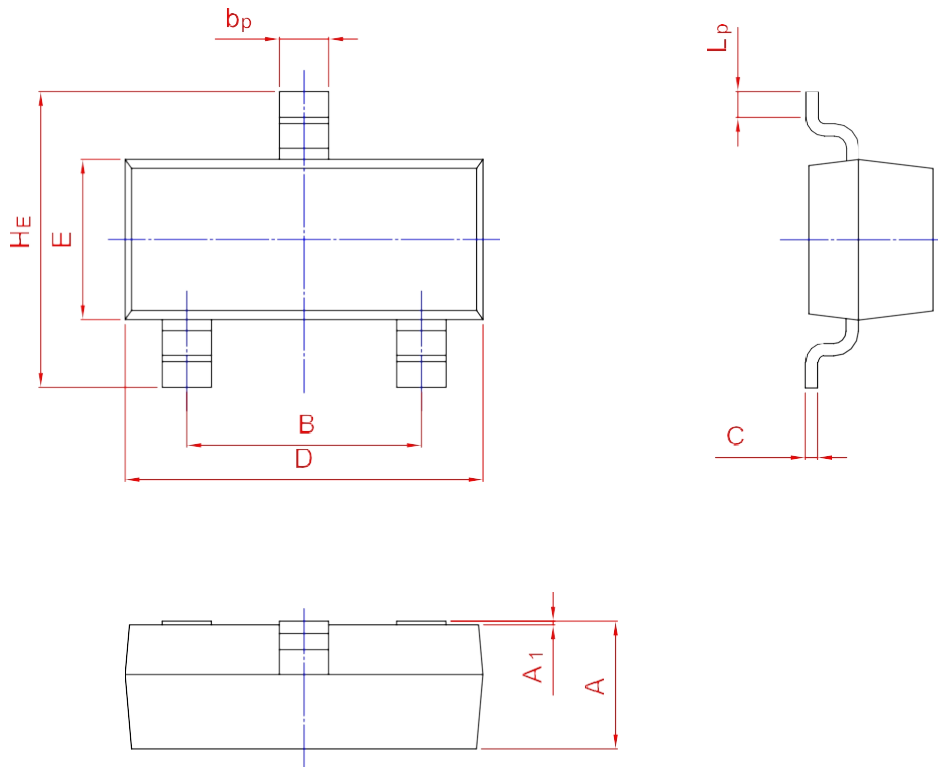
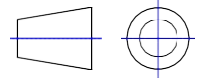
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20